

A METHOD AND STRUCTURE FOR LOW CAPACITANCE ESD ROBUST DIODES

Abstract of the Disclosure

A diode having a capacitance below 0.1pF and a breakdown voltage of at least 500V. The diode has an anode of a first conductivity type and a cathode of a second conductivity type disposed below the anode. At least one of the cathode and anode have multiple, vertically abutting diffusion regions. The cathode and anode are disposed between and bounded by adjacent isolation regions.

Figures

Figure 1: A line graph showing the relationship between the number of people in a household and the number of people in a household. The x-axis is labeled 'Number of people in a household' and ranges from 0 to 10. The y-axis is labeled 'Number of people in a household' and ranges from 0 to 10. The graph shows a positive linear relationship, with the line passing through the origin (0,0) and the point (10,10). The line is labeled 'y = x'.